

COMPLEMENTARY PAIR ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

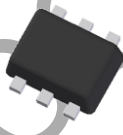
- Low On-Resistance
- Low Gate Threshold Voltage $V_{GS(TH)} < 1V$
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Complementary Pair MOSFET
- Ultra-Small Surface Mount Package
- ESD Protected Gate
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at <https://www.diodes.com/products/automotive/automotive-products/>.
- This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability. <https://www.diodes.com/quality/product-definitions/>

Mechanical Data

- Package: SOT563
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 
- Weight: 0.006 grams (Approximate)



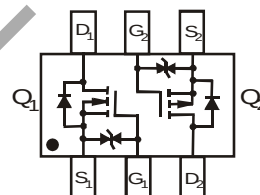
ESD Protected



Top View



Bottom View



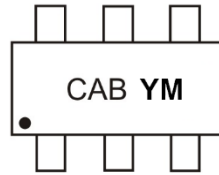
Top View
Internal Schematic

Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMC2004VK-7	SOT563	3000	Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



CAB = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: J = 2022)
 M = Month (ex: 9 = September)

Date Code Key

Year	2007		2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	U		J	K	L	M	N	O	P	R	S	T

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings N-CHANNEL – Q₁ (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain Source Voltage	V _{DSS}	20	V
Gate-Source Voltage	V _{GSS}	±8	V
Drain Current (Note 5)	I _D	T _A = +25°C: 670 T _A = +85°C: 480	mA

Maximum Ratings P-CHANNEL – Q₂ (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain Source Voltage	V _{DSS}	-20	V
Gate-Source Voltage	V _{GSS}	±8	V
Drain Current (Note 5)	I _D	T _A = +25°C: -530 T _A = +85°C: -380	mA

Thermal Characteristics

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P _D	0.45	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	281	°C/W
	t < 10s	210	°C/W
Total Power Dissipation (Note 6)	P _D	1	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	129	°C/W
	t < 10s	97	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

Electrical Characteristics N-CHANNEL – Q₁ (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	—	—	V	V _{GS} = 0V, I _D = 10μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1.0	μA	V _{DS} = 16V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±1.0	μA	V _{GS} = ±4.5V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	0.5	—	1.0	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	0.4 0.5 0.7	0.55 0.70 0.90	Ω	V _{GS} = 4.5V, I _D = 540mA V _{GS} = 2.5V, I _D = 500mA V _{GS} = 1.8V, I _D = 350mA
Forward Transfer Admittance (Note 8)	Y _{fs}	200	—	—	mS	V _{DS} = 10V, I _D = 0.2A
Diode Forward Voltage	V _{SD}	0.5	—	1.2	V	V _{GS} = 0V, I _S = 115mA
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	—	—	150	pF	V _{DS} = 16V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	—	25	pF	
Reverse Transfer Capacitance	C _{rss}	—	—	20	pF	

Electrical Characteristics P-CHANNEL – Q₂ (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1.0	μA	V _{DS} = -20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±1.0	μA	V _{GS} = ±4.5V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	-0.5	—	-1.0	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	0.7 1.1 1.7	0.9 1.4 2.0	Ω	V _{GS} = -4.5V, I _D = -430mA V _{GS} = -2.5V, I _D = -300mA V _{GS} = -1.8V, I _D = -150mA
Forward Transfer Admittance	Y _{fs}	200	—	—	mS	V _{DS} = 10V, I _D = 0.2A
Diode Forward Voltage	V _{SD}	-0.5	—	-1.2	V	V _{GS} = 0V, I _S = -115mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	—	175	pF	V _{DS} = -16V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	—	30	pF	
Reverse Transfer Capacitance	C _{rss}	—	—	20	pF	

Notes: 7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

Q1, N-CHANNEL

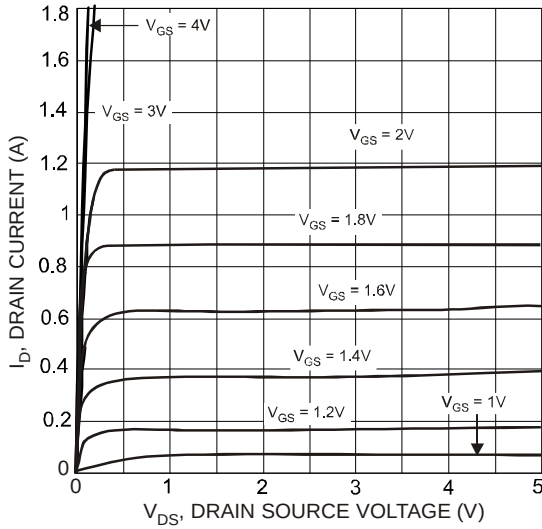


Fig. 1 Typical Output Characteristics

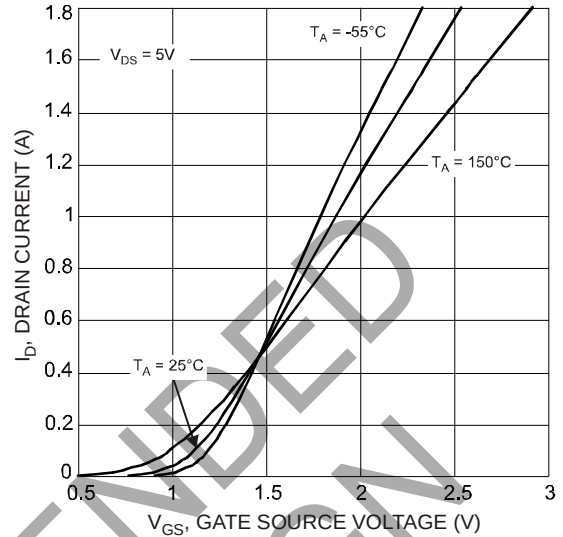


Fig. 2 Typical Transfer Characteristics

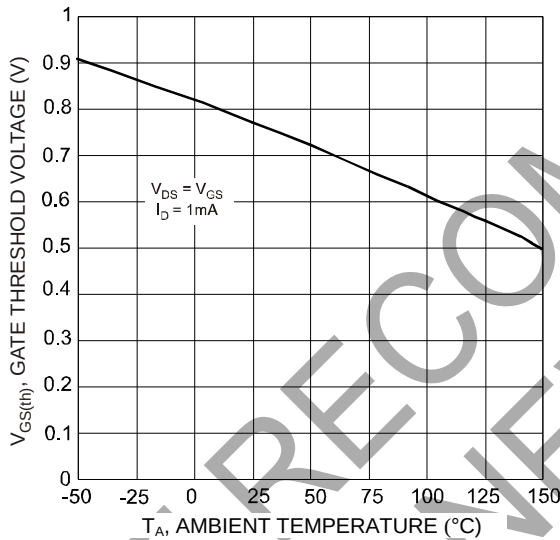


Fig. 3 Gate Threshold Voltage vs. Ambient Temperature

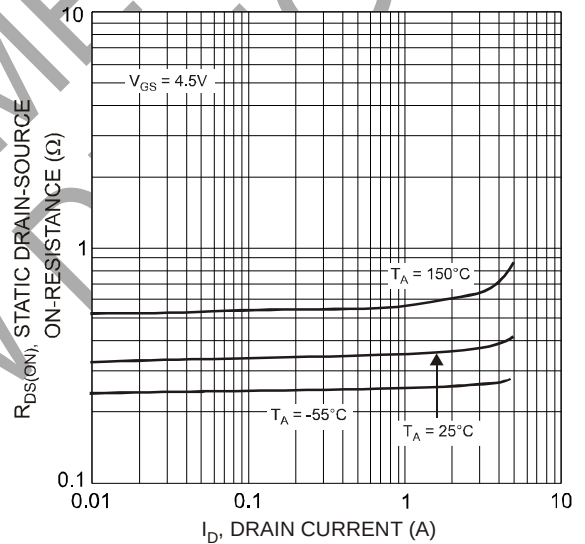


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

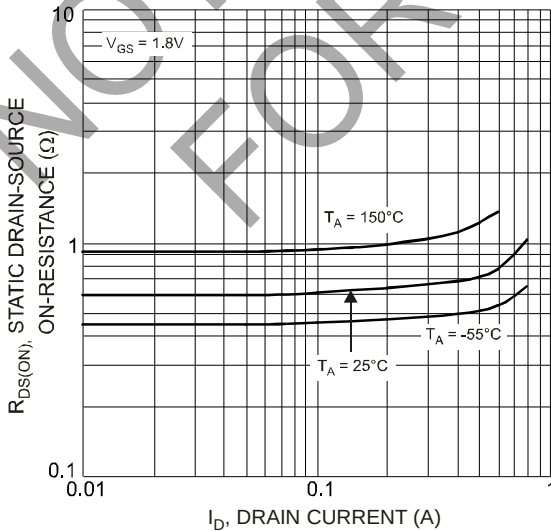


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current

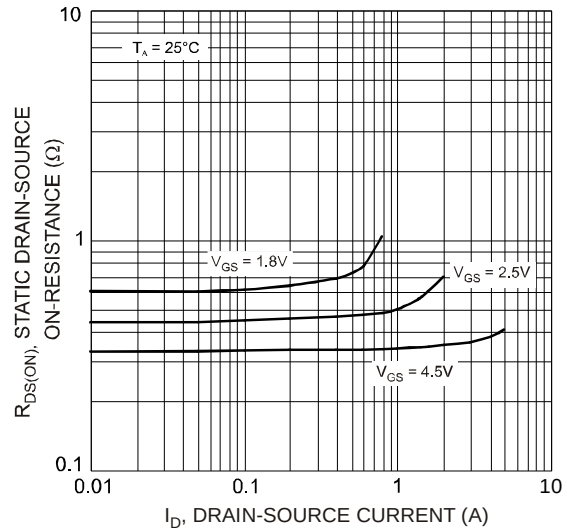


Fig. 6 Static Drain-Source On-Resistance vs. Drain-Source Current vs. Gate Source Voltage

Q1, N-CHANNEL (Continued)

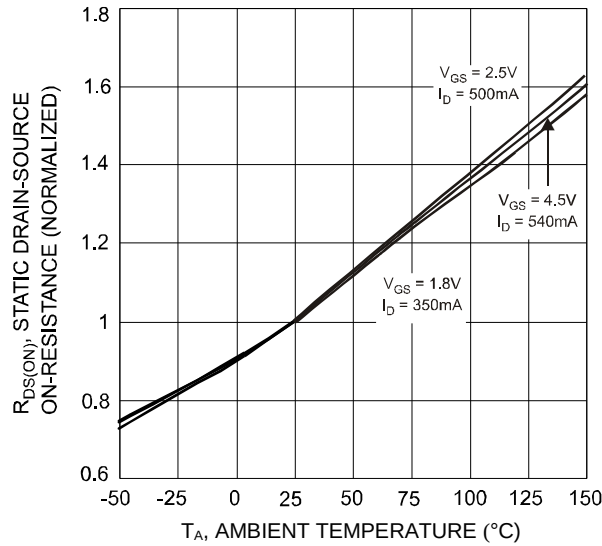


Fig. 7 Static Drain-Source On-State Resistance vs. Ambient Temperature

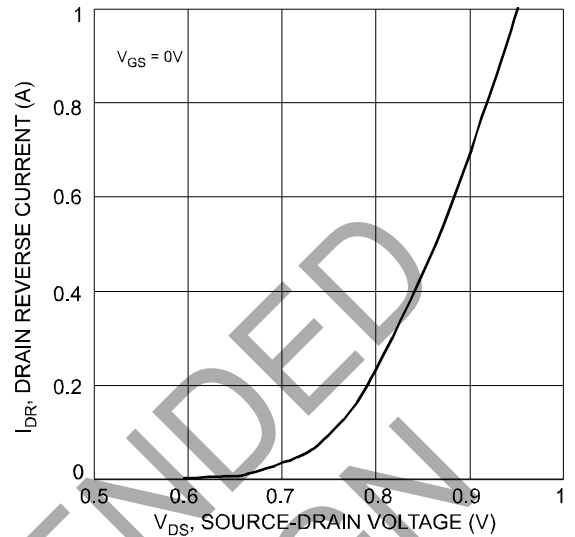


Fig. 8 Drain Reverse Current vs. Source-Drain Voltage

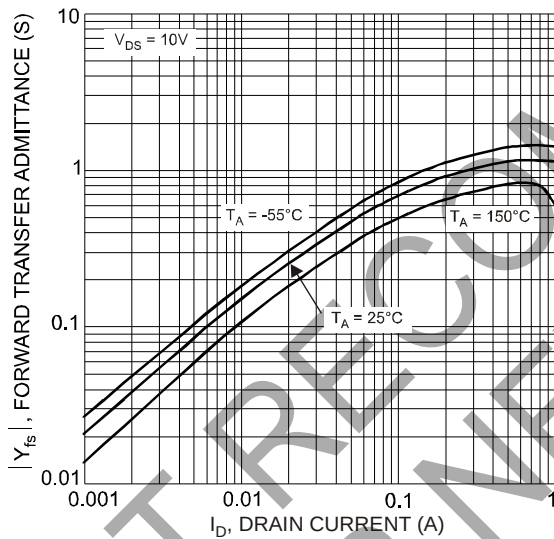


Fig. 9 Forward Transfer Admittance vs. Drain Current

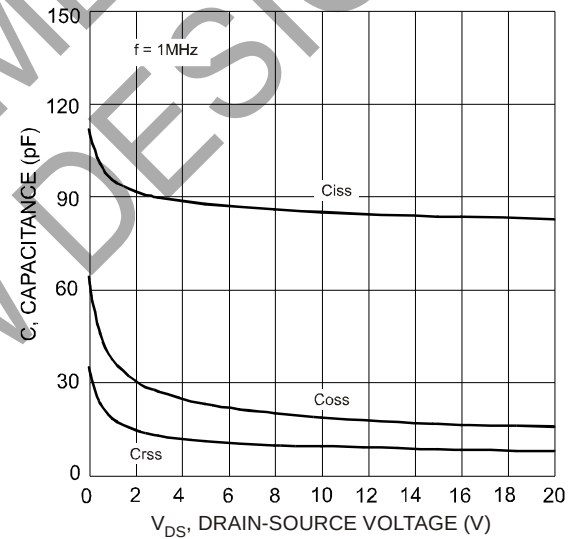


Fig. 10 Typical Capacitance

Q2, P-CHANNEL

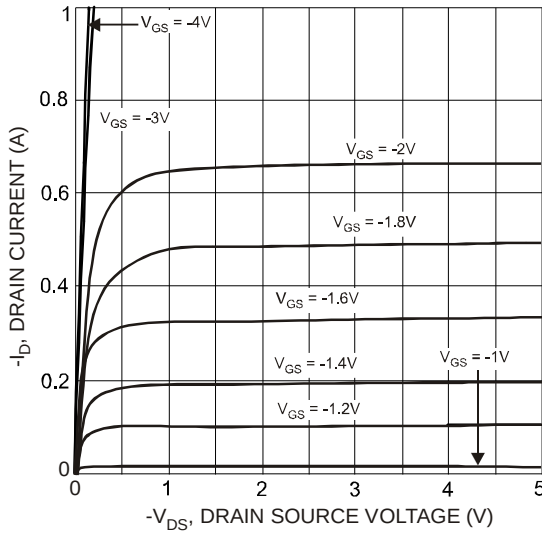


Fig. 11 Typical Output Characteristics

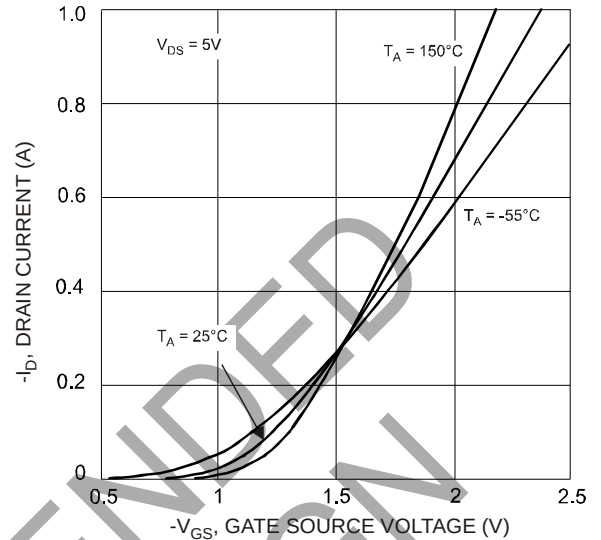


Fig. 12 Typical Transfer Characteristics

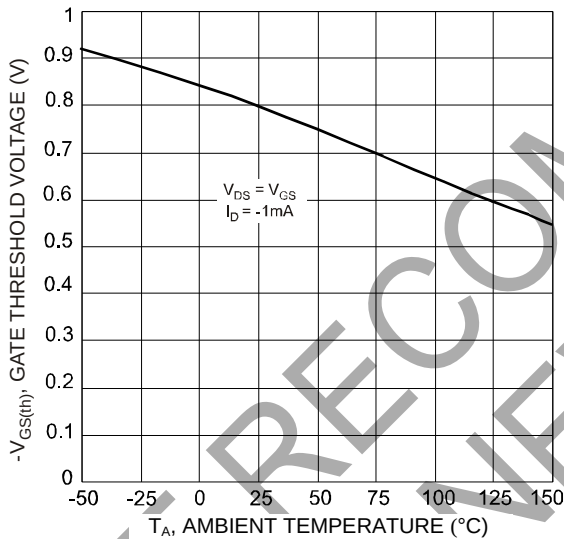


Fig. 13 Gate Threshold Voltage vs. Ambient Temperature

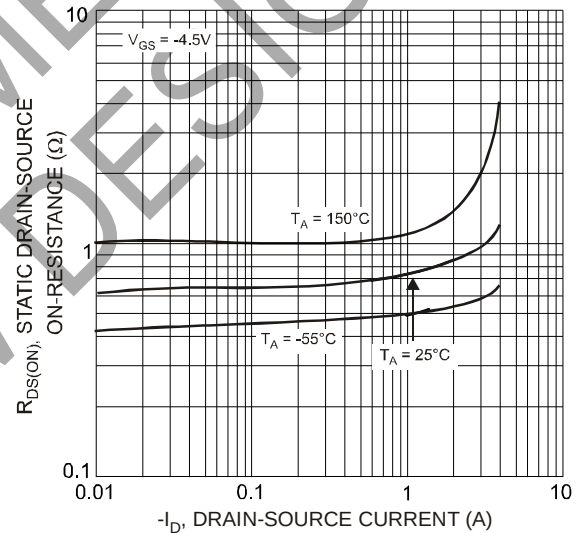


Fig. 14 Static Drain-Source On-Resistance vs. Drain Current

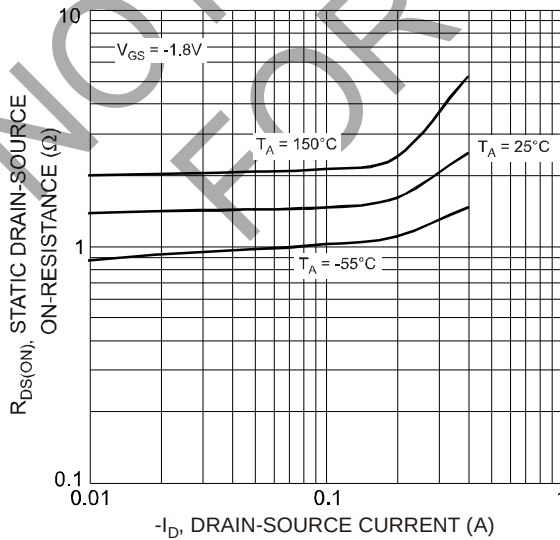


Fig. 15 Static Drain-Source On-Resistance vs. Drain Current

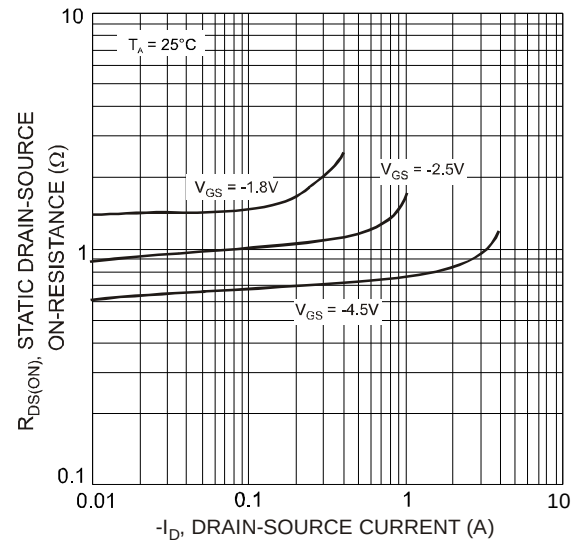


Fig. 16 Static Drain-Source On-Resistance vs. Drain-Source Current vs. Gate Source Voltage

Q₂, P-CHANNEL (Continued)

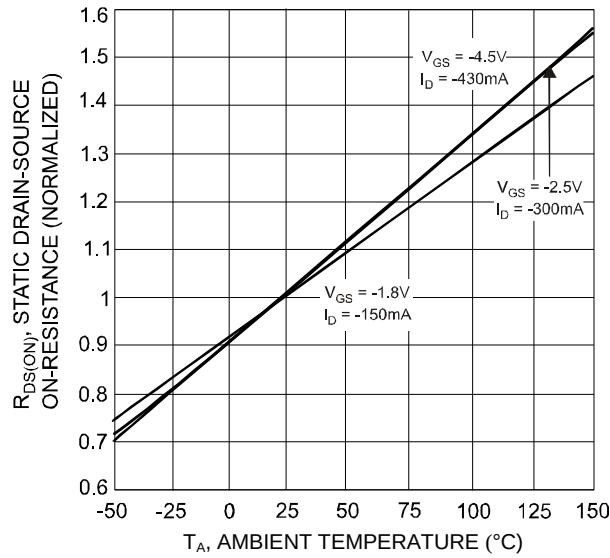


Fig. 17 Static Drain-Source On-State Resistance vs. Ambient Temperature

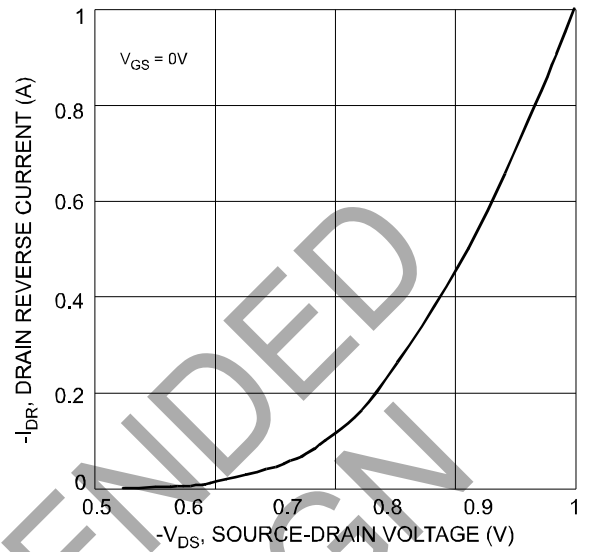


Fig. 18 Drain Reverse Current vs. Source-Drain Voltage

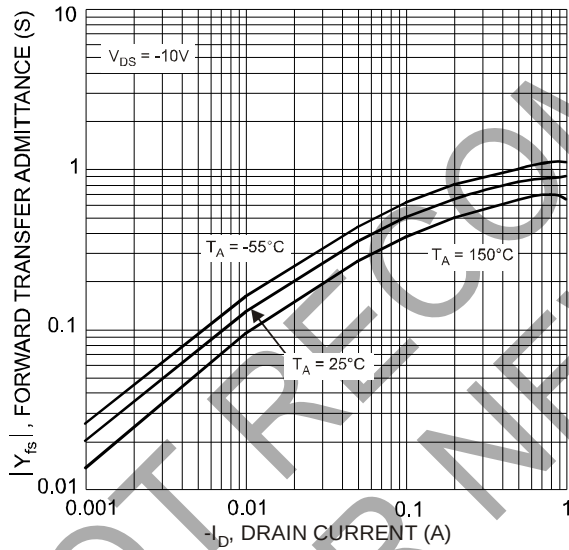


Fig. 19 Forward Transfer Admittance vs. Drain Current

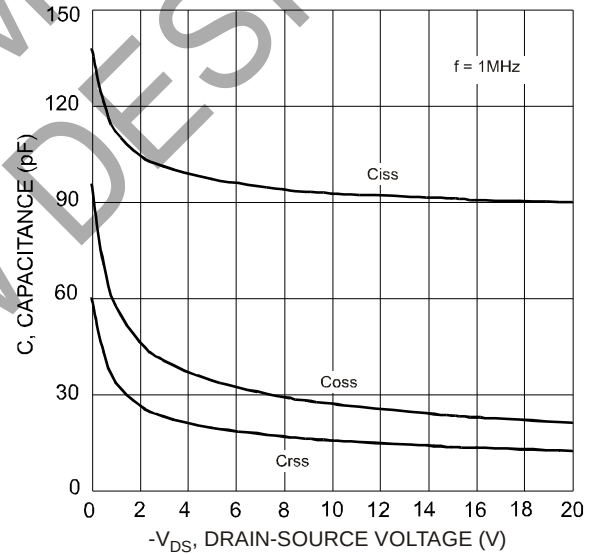
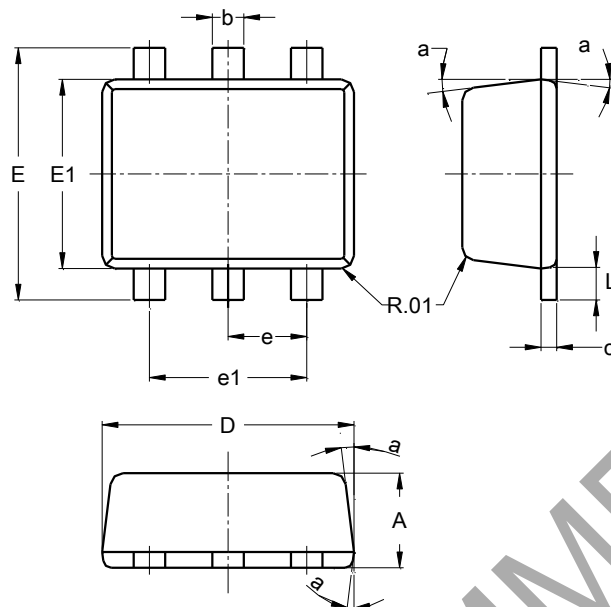


Fig. 20 Typical Capacitance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT563

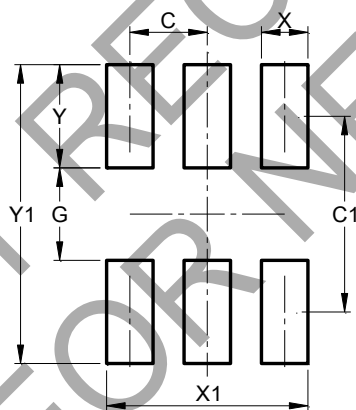


SOT563			
Dim	Min	Max	Typ
A	0.55	0.60	--
b	0.15	0.30	0.20
c	0.10	0.18	0.11
D	1.50	1.70	1.60
E	1.55	1.70	1.60
E1	1.10	1.25	1.20
e	--	--	0.50
e1	0.90	1.10	1.00
L	0.10	0.30	0.20
a	8°	9°	7°
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT563



Dimensions	Value (in mm)
C	0.500
C1	1.270
G	0.600
X	0.300
X1	1.300
Y	0.670
Y1	1.940

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